

## Supplementary material

# Following the Long-Term Evolution of $\text{sp}^3$ -type Defects in Tritiated Graphene using Raman Spectroscopy

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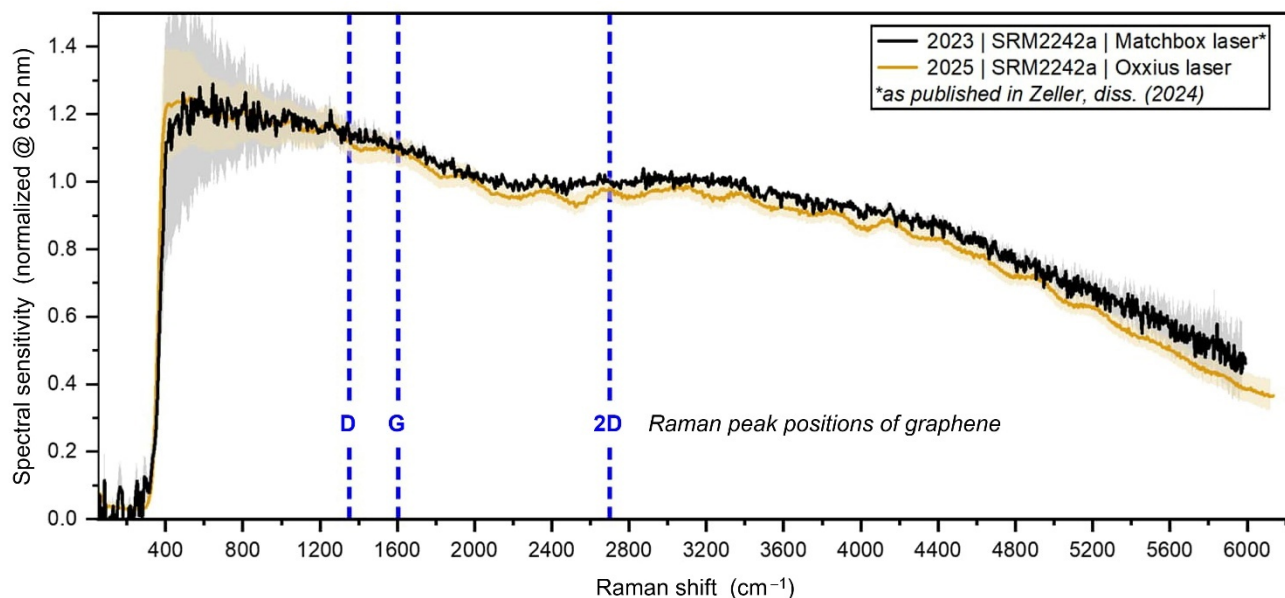
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## S1 – CRM Raman spectral sensitivity calibration based on the NIST SRM 2242a standard



**Figure S1:** Long-term stability and comparability of the Raman system, based on response measurements using the NIST SRM 2242a standard.<sup>39</sup> The sensitivity curves for different years and hardware configurations (including new gratings and a replaced laser) agree within 1 $\sigma$  uncertainties, demonstrating year-over-year cross-comparability. The curves are normalized to =1 at the wavelength of the fluorescence emission maximum of the standard.

## S2 – Representative Raman spectra for all samples, with Voigt fits to Raman features

For the fit procedure, pseudo-Voigt profile functions were utilised.<sup>40,41</sup> In an often-used mathematical description they are given as the linear combination

$$V(x; w_{(L)}, w_{(G)}) = \eta(r) \cdot L_V(x; w_{(V)}) + (1 - \eta(r)) \cdot G_V(x; w_{(V)}), \quad (1)$$

Its two common parameters are

- the width parameter  $\text{FWHM}_{(V)} \equiv w_{(V)} \approx 0.5346 \cdot w_{(L)} + \sqrt{w_{(G)} + 0.2166 \cdot w_{(L)}^2}$ , and

$$(2)$$

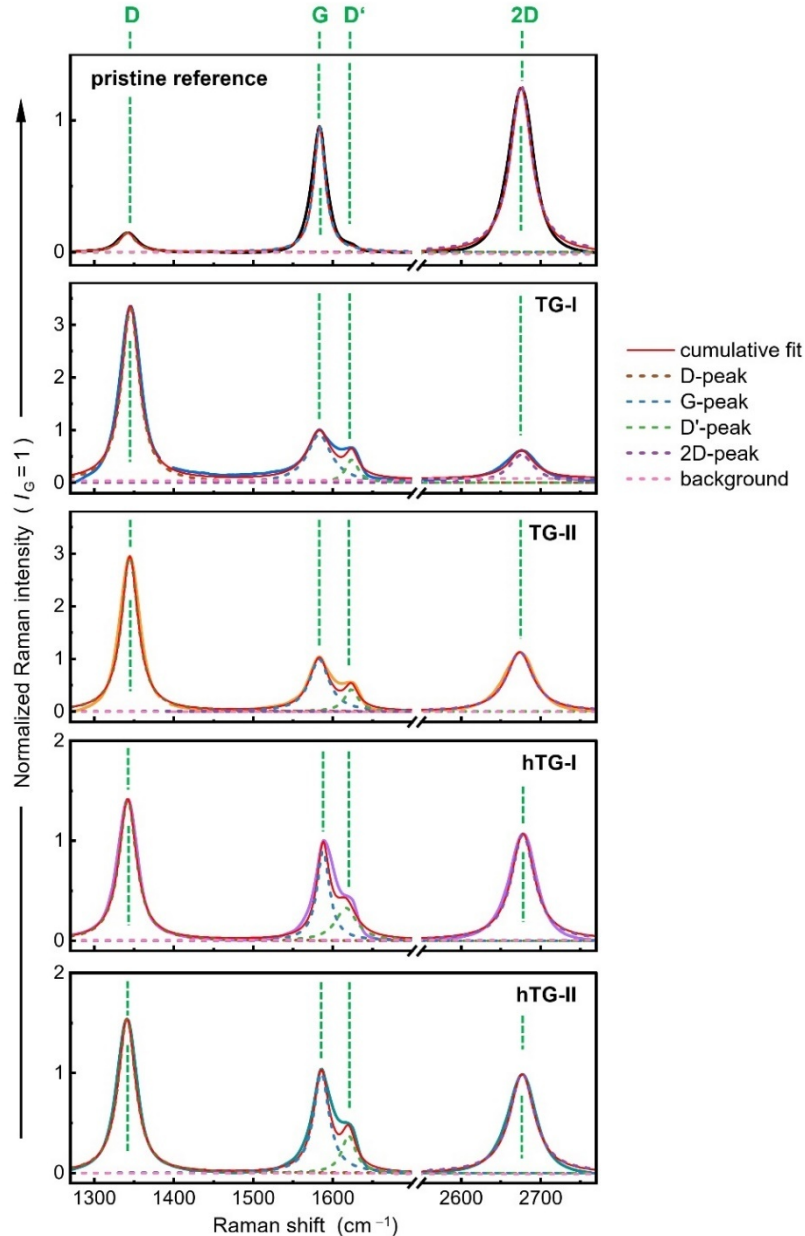
- the mixing parameter  $\eta(r) = 1.36603 \cdot r - 0.47719 \cdot r^2 + 0.11116 \cdot r^3$ , with  $r \equiv \frac{w_{(L)}}{w_{(V)}}$ .

$$(3)$$

Note that, in our fit implementation, the Lorentz ( $L$ ) and Gaussian ( $G$ ) component functions are taken in unit-height form and share the common width parameter,  $w_{(V)}$ ; thus, these line-shape functions are defined as

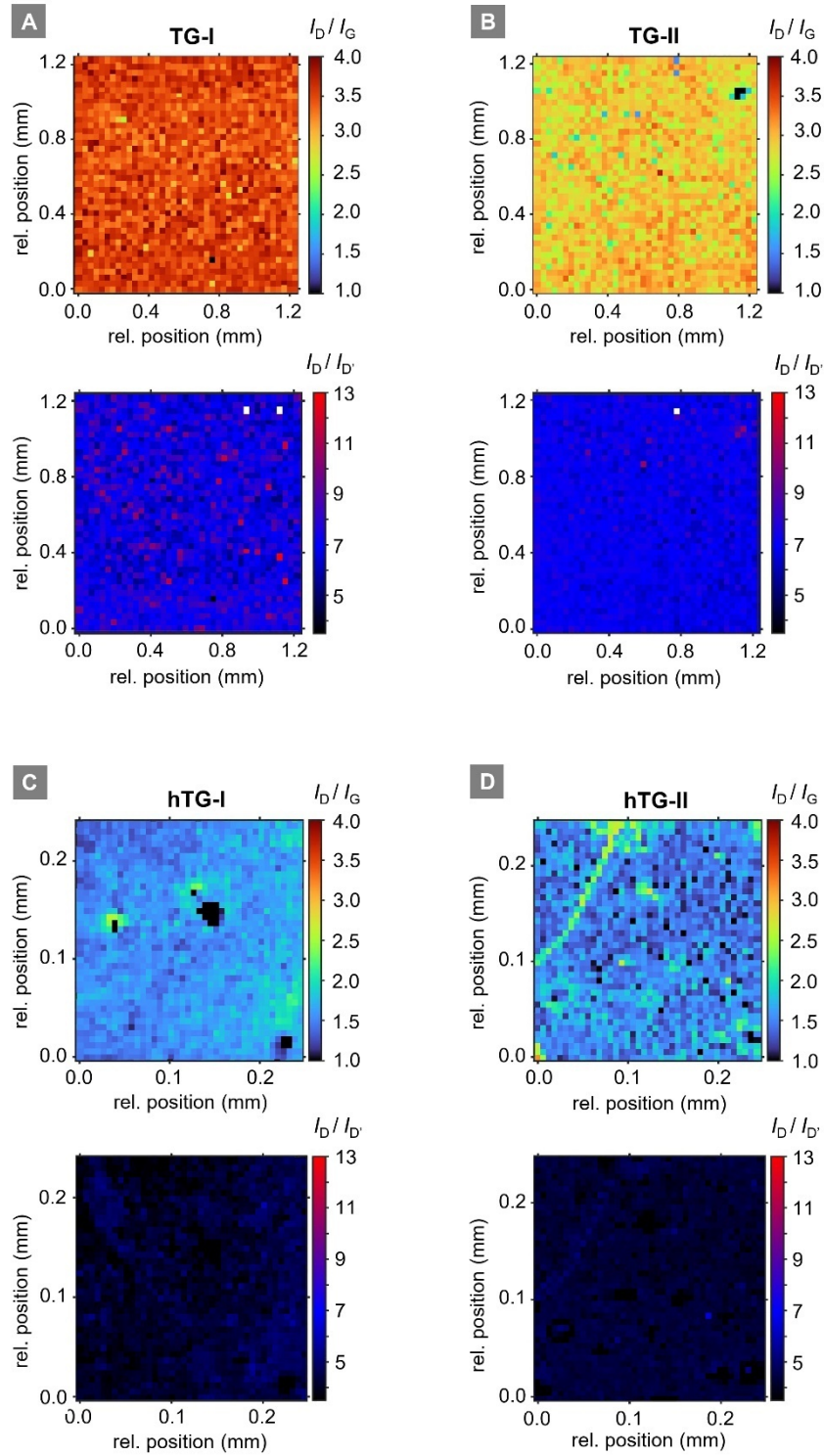
$$L(x; w_{(V)}) = \frac{w_{(V)}^2}{4 \cdot (x - x_c)^2 + w_{(V)}^2} \quad \text{and} \quad G(x; w_{(V)}) = \exp\left(-\frac{(x - x_c)^2}{2\sigma_{(G)}^2}\right). \quad (4)$$

Here the Gaussian component of  $V(x; w_{(L)}, w_{(G)})$  is associated with the resolution of the spectrometer, whose  $\text{FWHM}_{(G)}$  is evaluated from the analysis of the atomic line emission from a Ne-lamp (used for wavelength calibration of the spectrometer). For the spectrometer configuration used in campaign 0 this was  $\text{FWHM}_{(G)}(0) = 32 \pm 4 \text{ cm}^{-1}$ , while for campaigns I and II it was  $\text{FWHM}_{(G)}(\text{I,II}) = 9.6 \pm 0.7 \text{ cm}^{-1}$ .



**Figure S2:** Representative Raman spectra of all sample data sets (pristine, TG-I, TG-II, hTG-I and hTG-II), shown with individual Voigt peak-fits and cumulative fit results. TG = tritiated graphene; hTG = heated tritiated graphene.

### S3 – Information extracted from the Raman spectroscopic maps of the samples

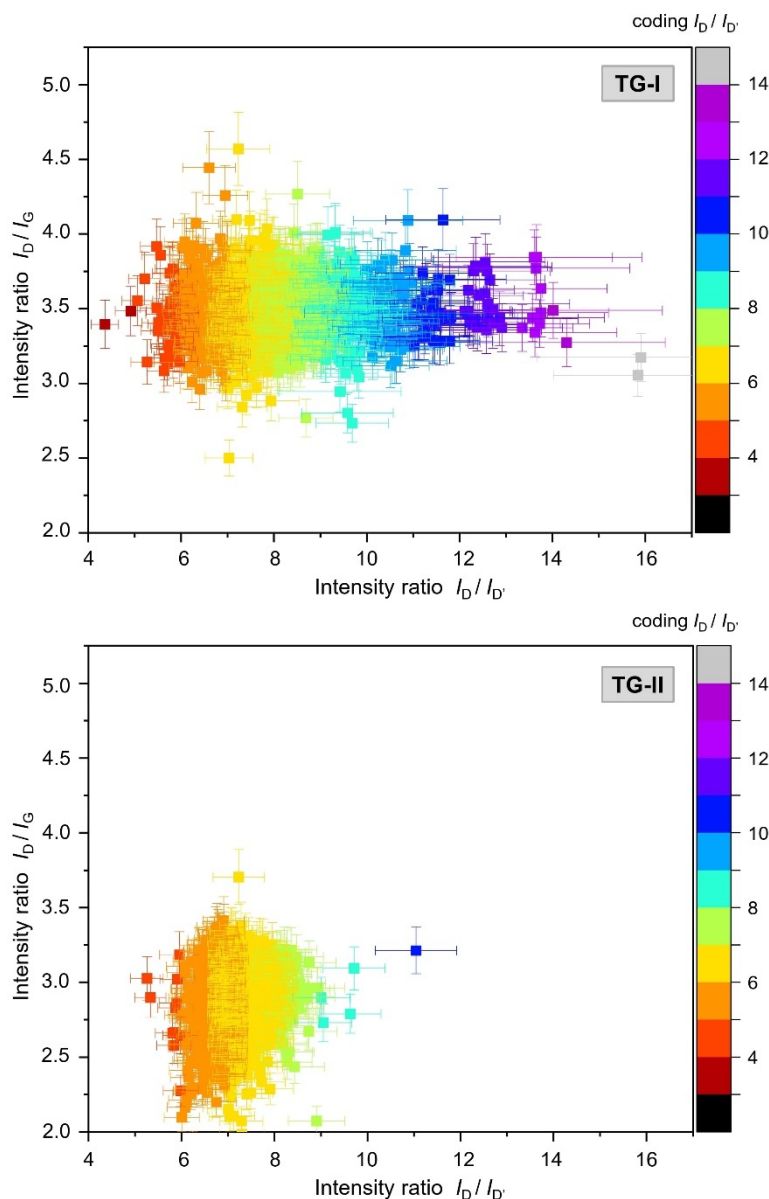


**Figure S3:** Raman spectroscopic maps of all graphene samples. Note that the one-year-later maps were not recorded for exactly equal areas of the samples. Top rows:  $I_D/I_G$  intensity ratios; bottom rows:  $I_D/I_{D'}$  intensity ratios.

- (A)  $1.2 \times 1.2 \text{ mm}^2$  area scan with step size of  $\Delta S=32 \text{ }\mu\text{m}$  of  $T_2$ -exposed graphene.
- (B)  $1.2 \times 1.2 \text{ mm}^2$  area scan with step size of  $\Delta S=32 \text{ }\mu\text{m}$  of  $T_2$ -exposed graphene, after one year of storage in laboratory atmosphere.
- (C)  $0.25 \times 0.25 \text{ mm}^2$  area scan with step size of  $\Delta S=7 \text{ }\mu\text{m}$  of  $T_2$ -exposed graphene, heated at  $500 \text{ }^\circ\text{C}$  for 24 h.
- (D)  $0.25 \times 0.25 \text{ mm}^2$  area scan with step size of  $\Delta S=7 \text{ }\mu\text{m}$  of heated  $T_2$ -exposed graphene, after one year of storage in laboratory atmosphere.

### S3.1 Numerical values for all Raman map points, and their graphical representation

From the line ratio maps for the D-, D'- and G-peaks displayed in Figure S3 one can extract the actual numerical values, and plot these in the form  $I_D/I_G$  versus  $I_D/I_{D'}$ . This plot is shown in Figure S4. Note that Figure 4 in the main text is a simplified representation of these data, in the form of a contour plot, lumping data points together around the mean (as  $1\sigma$ -,  $2\sigma$ - and  $3\sigma$  contours regions).



**Figure S4:** Intensity ratio plots of  $I_D/I_G$  versus  $I_D/I_{D'}$  of the  $40 \times 40$  data points from the Raman maps in Figures S3(a) and S3(b), including error bars for each individual data point.

Note that in the figure the D/D' classification values are colour-coded according to integer-value ranges (analogous to the defect-type limiters).

For classification and interpretation, the values for each integer range are summed up, and the sum-values are shown as relative fractions of the total in Figure 6 of the main text. Said diagram serves as a visualisation aid in the discussion of the defect-type densities.

All (mean) evaluation parameters used for the presentation and interpretation of the experimental data – i.e., numerical values (including errors) for peak position, peak width and intensity ratios for the relevant Raman features G, D, D' and 2D – are summarised in Table S1.

**Table S1:** Mean fit results for all data sets. Given uncertainties are calculated from individual per spectra uncertainties,  $\bar{u}_i$ , and spread of the data points,  $s$ :  $\sigma_{\text{tot}} = (\bar{u}_i^2 + s^2)^{1/2}$ . Note that, the individual uncertainties are much smaller than the spread of the data points within each data set, therefore, in first order, one can approximate  $\sigma_{\text{tot}} \approx s$ . The mixing parameter is defined in equation (4) of S2.

	Peaks	Pristine	TG-I	TG-II	hTG-I	hTG-II
Intensity ratio	D/G	0.12 ± 0.01	3.51 ± 0.26	2.90 ± 0.28	1.60 ± 0.24	1.53 ± 0.29
	D'/G	0.02 ± 0.01	0.49 ± 0.07	0.42 ± 0.05	0.38 ± 0.06	0.37 ± 0.11
	D/D'	6.22 ± 1.50	7.18 ± 1.00	6.94 ± 0.56	4.22 ± 0.50	4.26 ± 0.32
	2D / G	1.75 ± 0.10	0.70 ± 0.09	1.28 ± 0.27	1.36 ± 1.08	1.15 ± 0.16
	D / 2D	0.07 ± 0.01	5.07 ± 0.57	2.32 ± 0.37	1.22 ± 0.31	1.41 ± 0.71
FWHM <sub>(L)</sub> in cm <sup>-1</sup>	D (w <sub>D</sub> )	54.2 ± 5.5	28.8 ± 1.3	27.4 ± 1.2	29.3 ± 3.5	31.8 ± 7.1
	G (w <sub>G</sub> )	16.3 ± 0.9	39.7 ± 6.2	33.8 ± 3.4	21.3 ± 4.0	26.5 ± 6.0
	D' (w <sub>D'</sub> )	21.8 ± 17.5	21.1 ± 6.5	22.4 ± 2.7	32.8 ± 8.7	23.6 ± 3.6
	2D (w <sub>2D</sub> )	32.9 ± 0.7	41.6 ± 6.6	44.8 ± 6.7	37.4 ± 4.3	39.0 ± 6.0
Position in cm <sup>-1</sup>	D	1344.7 ± 1.2	1344.5 ± 3.3	1342.9 ± 0.8	1329.3 ± 1.3	1339.6 ± 4.7
	G	1584.5 ± 0.9	1581.9 ± 3.9	1581.0 ± 1.3	1572.6 ± 1.5	1583.4 ± 5.6
	D'	1621.1 ± 5.3	1622.7 ± 4.0	1621.8 ± 1.3	1601.3 ± 1.5	1618.7 ± 5.7
	2D	2677.0 ± 1.8	2674.0 ± 6.7	2672.7 ± 1.6	2652.2 ± 2.6	2673.8 ± 20.3
Mixing parameter $\eta$	D	0.98 ± 0.01	0.93 ± 0.02	0.92 ± 0.01	0.92 ± 0.09	0.93 ± 0.03
	G	0.83 ± 0.01	0.95 ± 0.03	0.94 ± 0.01	0.87 ± 0.09	0.91 ± 0.04
	D'	0.83 ± 0.11	0.86 ± 0.07	0.89 ± 0.02	0.92 ± 0.10	0.89 ± 0.04
	2D	0.94 ± 0.01	0.96 ± 0.03	0.97 ± 0.00	0.94 ± 0.09	0.95 ± 0.04

### S3.2 Concept for the determination of the concentrations of defect types

By and large, defect types (x) may be separated into two broad classes, namely adsorption-type ( $x \equiv a$ ) and vacancy-type ( $x \equiv v$ ) defects. According to established, descriptive models for defects in graphene they manifest themselves in changes in the amplitude and shape of Raman spectral features. For stage-1 defect-density samples, i.e., samples with small to moderate defect densities, one can take away two key messages (based on said models):

- (i) the intensity ratio  $I_D/I_G$  is proportional to the defect density,  $L_D(x)$ , in units of (nm); and
- (ii) the intensity ratio  $I_D/I_{D'}$  yields distinct associations:  $I_D/I_{D'} \geq 13$  is indicative for adsorption defects;  $I_D/I_{D'} \leq 7$  for vacancy defects; and  $I_D/I_{D'}$  in the range 7...13 for mixed defects.

Note however that, mixing cannot necessarily be assumed to be linear.

The established model for vacancy-type defects is that by Lucchese and co-workers,<sup>32</sup> which was generalized for different laser excitation energies,  $E_L$  (in eV), by Cançado and co-workers.<sup>33</sup> The latter describes the relationship between  $I_D/I_G$  and  $L_D(v)$  as

$$\frac{I_D}{I_G}(L_D) = C_A \frac{r_A^2 - r_S^2}{r_A^2 - 2r_S^2} \cdot \left[ e^{-\pi \frac{r_S^2}{L_D^2}} - e^{-\pi \frac{r_A^2 - r_S^2}{L_D^2}} \right] + C_S \left[ 1 - e^{-\pi \frac{r_S^2}{L_D^2}} \right] \quad (5)$$

with  $C_A = 160 \cdot E_L^{-4} \cdot \text{eV}^{-4}$ ,  $C_S = 0.87 \pm 0.05$ ,  $r_A = (3.00 \pm 0.03) \text{ nm}$ , and  $r_S = (1.00 \pm 0.04) \text{ nm}$ .

Recently Fournier and co-workers published a model specifically tailored for  $sp^3$ -type defects.<sup>36</sup> There the relationship between  $I_D/I_G$  and  $L_D(a)$  is defined by

$$\frac{I_D}{I_G}(L_D) = \frac{C_S f_S(L_D) + C_A f_A(L_D)}{1 - f_{sp^3}(L_D)}, \quad (6)$$

where

$$f_A(L_D) = e^{-\pi \frac{r_S^2}{L_D^2}} - e^{-\pi \frac{r_A^2}{L_D^2}}, \quad f_S(L_D) = e^{-\pi \frac{r_{sp^3}^2}{L_D^2}} - e^{-\pi \frac{r_S^2}{L_D^2}} \quad \text{and} \quad f_{sp^3}(L_D) = 1 - e^{-\pi \frac{r_{sp^3}^2}{L_D^2}}, \quad (7)$$

and  $C_A = 20.1$ ,  $C_S = 0.86$ ,  $r_A = 0.242 \text{ nm}$ ,  $r_S = 0.183 \text{ nm}$  and  $r_{sp^3} = 0.0913 \text{ nm}$ .

When evaluating and comparing our data – using these two models – one finds that, the Raman response to the two defect types is significantly more sensitive for vacancy-type defects than for adsorption-type defects. For example, a value of  $I_D/I_G = 0.1$  would correspond to

$$L_D(\text{Lucchese / Cançado}) = 37.1 \text{ nm} , \text{ or}$$

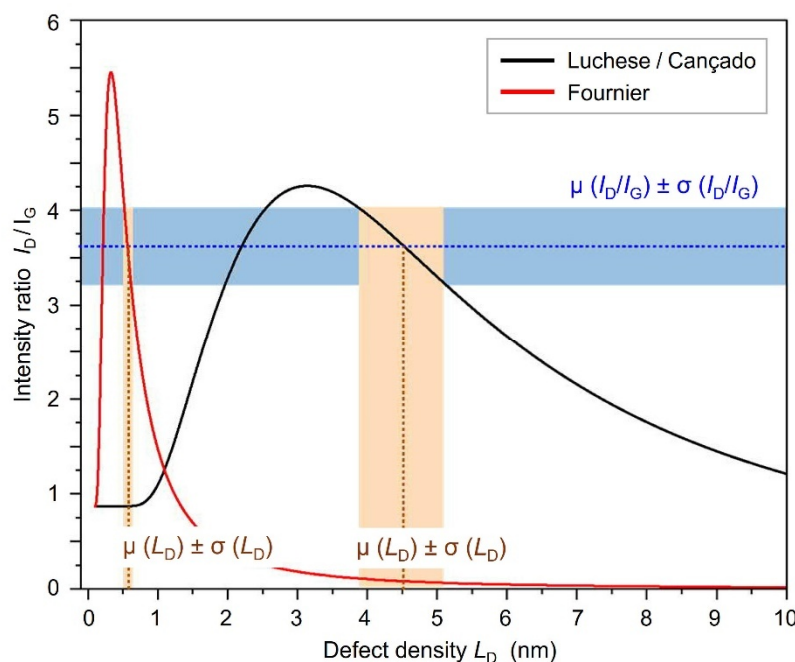
$$L_D(\text{Fournier}) = 4.1 \text{ nm} .$$

This means that, when quantitatively comparing data sets, for compositional changes, both variations in  $I_D/I_G$  and  $I_D/I_D$  need to be tracked in parallel.

### S3.3 Example calculation

Simplified versions of the complex equations (1) and (2) can be found in the literature, which allow for an analytical inversion; however, these are in general only applicable in the low-defect density regime. Since this is not the case for the samples studied in this work, we use a different approach.

In order to accurately evaluate the defect density,  $L_D$ , from the intensity ratio,  $I_D/I_G$ , we calculate the correlation curves according to the two models, and then perform numerical interpolation. This principle is visualised for the TG-I data in Figure S5.



**Figure S5:** Calculated numerical  $I_D/I_G$  vs  $L_D$  curves, according to the models of Lucchese/Cançado and Fournier. The blue dotted line and the blue band correspond to the mean  $I_D/I_G$  with  $1\sigma$  standard uncertainty of the TG-I data set. As it is shown in the main document, the TG-I data fall to the low-defect regime (Stage 1); therefore, the crossing at smaller  $L_D$ -values is correct here. The orange lines and bands visualise the  $L_D$ -values and their uncertainties; they are obtained by numerically interpolating the intersection points with the blue line, and their uncertainty, for each of the two model curves.

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